

6L& 6FKRWWN\ %DUULHU 'LRGH

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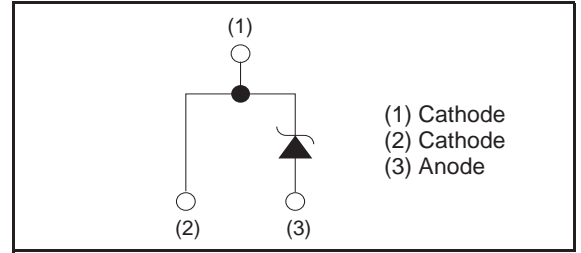
) HDWXUHV

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Silicon carbide epitaxial planar type

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Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
DC blocking voltage	V_{DC}	$I_R=30 \text{ mA}$	650	-	-	V
		$I_F=6\text{A}, T_j=25^\circ\text{C}$	-	1.35	1.50	V
Forward voltage	V_F	$I_F=6\text{A}, T_j=150^\circ\text{C}$	-	1.44	1.71	V
		$I_F=6\text{A}, T_j=175^\circ\text{C}$	-	1.50	-	V
Reverse current	I_R	$V_R=650\text{V}, T_j=25^\circ\text{C}$	-	0.018	30	mA
		$V_R=650\text{V}, T_j=150^\circ\text{C}$	-	1.2	120	mA
		$V_R=650\text{V}, T_j=175^\circ\text{C}$	-	3.6	-	mA
		$V_R=650\text{V}, f=1\text{MHz}$	-	7	-	pF



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Symbol	Typical Value	Unit
a_0	9.66E-01	V
a_1	1.10E-03	V/°C
b_0	5.87E-02	:
b_1	1.24E-04	:/°C
b_2	1.28E-06	:/°C ²